

# YJ Planar Schottky Barrier Diode Die Specification

100V 5A, 68mil, Schottky barrier diode die based on silicon planar process  
Part No.: PSB068S100SS-280A

## Main Products Characterstics

### Maximum Ratings

### Static Electrical Characteristics (Ta = 25°C)

$I_F = 5\text{ A}$   
 $\leq 2\%$

## Device Schematics and Outline Drawing

- Die Thickness \*
- Die Size \*\*
- Top Metal Pad
- Active Area
- Top Metal
- Back Metal
- Note: 1 \* : Also can offer device with 8 mils thickness
- 2 \*\*: Cutting street width is around 1.5 mils

## Important Notice

Specification apply to die only. Actual performance may degrade when assembled. Recommended Storage Environment:  
does not guarantee device performance after 330 days of storage. (x-none) BDC 49.16 70.8 530.5 7048 reWBTF3 6.72 Tf1 0 0 1 87.02493.3